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ADC128S102QML-SP

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# ADC128S102QML-SP Radiation Hardened 8-Channel, 50 kSPS to 1 MSPS, 12-Bit A/D Converter

#### Features 1

- 5962R07227
  - Total Ionizing Dose 100 krad(Si)
  - Single Event Latch-Up Immune 120 MeVcm<sup>2</sup>/mg
  - Single Event Functional Interrupt Immune 120 MeV-cm<sup>2</sup>/mg
  - (See Radiation Report)
- **Eight Input Channels** •
- Variable Power Management
- Independent Analog and Digital Supplies
- SPI™/QSPI™/MICROWIRE™/DSP Compatible
- Packaged in 16-Lead Ceramic SOIC
- **Key Specifications** 
  - Conversion Rate: 50 kSPS to 1 MSPS
  - − DNL (V<sub>A</sub> = V<sub>D</sub> = 5 V): +1.5 / −0.9 LSB (Maximum)
  - INL ( $V_A = V_D = 5 V$ ): +1.4 / -1.25 LSB (Maximum)
  - Power Consumption
    - 3-V Supply: 2.3 mW (Typical)
    - 5-V Supply: 10.7 mW (Typical)

# 2 Applications

- Satellites
  - Attitude and Orbit Control
  - **Precision Sensors**
  - Motor Control
- **High Temperature**
- Medical Systems
- Accelerators

# 3 Description

The ADC128S102 device is a low-power, eightchannel CMOS 12-bit analog-to-digital converter specified for conversion throughput rates of 50 kSPS to 1 MSPS. The converter is based on a successiveapproximation register architecture with an internal track-and-hold circuit. The device can be configured to accept up to eight input signals at inputs INO through IN7.

Support &

Community

The output serial data is straight binary and is compatible with several standards, such as SPI, QSPI, MICROWIRE, and many common DSP serial interfaces.

The ADC128S102 may be operated with independent analog and digital supplies. The analog supply  $(V_A)$ can range from 2.7 V to 5.25 V, and the digital supply  $(V_D)$  can range from 2.7 V to  $V_A$ . Normal power consumption using a 3-V or 5-V supply is 2.3 mW and 10.7 mW, respectively. The power-down feature reduces the power consumption to 0.06 µW using a 3-V supply and 0.25 µW using a 5-V supply.

#### Device Information<sup>(1)</sup>

PART NUMBER	GRADE	PACKAGE				
ADC128S102WGRQV	5962R0722701VZA 100 krad	16-lead ceramic SOIC				
ADC128S102WRQV	5962R0722701VFA 100 krad	16-lead ceramic flatpack				
ADC128S102-MDR	5962R0722701V9A 100 krad	Die				
ADC128S102WGMPR	Pre-Flight Engineering Prototype	16-lead ceramic SOIC				
ADC128S102CVAL	Ceramic Evaluation Board					

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Block Diagram**



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# **Table of Contents**

1	Feat	tures 1
2	Арр	lications 1
3		cription 1
4		ision History 2
5	Pin	Configuration and Functions 4
6	Spe	cifications5
	6.1	Absolute Maximum Ratings 5
	6.2	ESD Ratings5
	6.3	Recommended Operating Conditions 5
	6.4	Thermal Information 6
	6.5	Electrical Characteristics: ADC128S102QML-SP Converter
	6.6	Electrical Characteristics: Radiation
	6.7	Electrical Characteristics: Burn in Delta Parameters - $T_A$ at 25°C
	6.8	Timing Requirements
	6.9	Typical Characteristics 11
7	Deta	ailed Description 16
	7.1	Overview
	7.2	Functional Block Diagram 16
	7.3	Feature Description 16
	7.4	Device Functional Modes 18

	7.5	Programming	19
8	App	lication and Implementation	21
	8.1	Application Information	21
	8.2	Typical Application	21
9	Pow	er Supply Recommendations	23
	9.1	Power Supply Sequence	
	9.2	Power Management	23
	9.3	Power Supply Noise Considerations	23
10	Lay	out	24
	10.1	Layout Guidelines	24
	10.2	Layout Example	24
11	Dev	ice and Documentation Support	25
	11.1	Device Support	25
	11.2	Receiving Notification of Documentation Updates	26
	11.3	Community Resources	26
	11.4	Trademarks	26
	11.5	Electrostatic Discharge Caution	26
	11.6	Glossary	26
12	Mec	hanical, Packaging, and Orderable	
	Info	rmation	27
	12.1	Engineering Samples	27

# 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision O (November 2016) to Revision P Page
•	Changed feature link from 5962R07727 to 5962R072271
CI	hanges from Revision N (September 2015) to Revision O Page
•	Changed the title of the ADC128S102QML-SP data sheet 1
•	Added Radiation Report link to Features
•	Changed Applications1
•	Changed Device Information table
•	Added 14-pin CFP package option to the data sheet 1
•	Added TYPE column to the Pin Functions table
•	Added tablenote for digital supply voltage maximums allowed in the Absolute Maximum Ratings table
•	Updated maximum tablenote for the digital supply voltage in the Absolute Maximum Ratings table
•	Added tablenote for the voltage on any pin to GND maximums allowed in the Absolute Maximum Ratings table
•	Added links to the Quality Conformance Inspection table to the Electrical Characteristics tables
•	Added MIN and MAX test conditions for the SCLK duty cycle in the <i>Electrical Characteristics: ADC128S102QML-SP</i> Converter table
•	Changed ADC128S102 Operational Timing Diagram image
•	Changed first sentence and added MIL-STD-883G, Test Method 1019.7 link to the <i>Total Ionizing Dose</i> section
•	Changed total ionizing dose rate from 0.16 to 0.027 rad(Si)/s
•	Changed Single Event Latch-Up section to Single Event Latch-Up and Functional Interrupt
•	Added sentence to Serial Interface section: Note that $\overline{CS}$ is asynchronous
•	Added Engineering Samples section

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SNAS411P - AUGUST 2008 - REVISED APRIL 2017

Changes from Revision H (October 2009) to Revision N	Page
<ul> <li>Added Pin Configuration and Functions section, ESD Ratings table, Feature Description section, Device Functiona Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section</li> </ul>	
Changes from Revision G (October 2009) to Revision H	Page
Added reference to Note 11.	5
Added Note:11	5
Deleted 'TYPICAL' numbers from t <sub>DHID</sub> , t <sub>DS</sub> and t <sub>DH</sub>	6
Changed Min limit on t <sub>DHID</sub> from 11 to 7	6
Changes from Revision F (June 2009) to Revision G	Page
Deleted reference to Ta Min and Ta Max under titled sections.	6
Changes from Revision E (April 2009) to Revision F	Page
Changed AC Electrical Characteristics - SCLK Duty Cycle, typ limits	8
Changes from Revision C (November 2008) to Revision D	Page
Moved Rad information from Key Specifications to Features	1
Deleted ADC128S102WGMLS reference	6
Added Burn In Delta Table	9
Changes from Revision B (August 2008) to Revision C	Page
Corrected package reference from 16-lead TSSOP to 16-lead Ceramic SOIC, Removed QV NSID reference and Added SMD Number to RQV NSID in <i>Features</i> .	1
Changes from Revision A (August 2008) to Revision B	Page
Typo, Changed Figure 2, t <sub>DIS</sub> lower left hand side changed to t <sub>DS</sub> and t <sub>DIH</sub> lower left hand side change to t <sub>DH</sub> in Timing Diagrams.	10



# 5 Pin Configuration and Functions



#### Pin Functions

PIN		ТҮРЕ	DESCRIPTION
NAME	NO.	ITPE	DESCRIPTION
ANALOG I/O			
	4		
	5		
	6		
IN0 to IN7	7	Input	Angles issues. These signals can rease from 0.1/ to 1/
INU TO IN7	8	(Analog)	Analog inputs. These signals can range from 0 V to V <sub>REF</sub> .
	9		
	10	10	
	11		
DIGITAL I/O			
CS	1	Input (Digital)	Chip select. On the falling edge of $\overline{CS}$ , a conversion process begins. Conversions continue as long as $\overline{CS}$ is held low.
DIN	14	Input (Digital)	Digital data input. The ADC128S102QML-SP's Control Register is loaded through this pin on rising edges of the SCLK pin.
DOUT	15	Output (Digital)	Digital data output. The output samples are clocked out of this pin on the falling edges of the SCLK pin.
SCLK	16	Input (Digital)	Digital clock input. The specified performance range of frequencies for this input is 0.8 MHz to 16 MHz. This clock directly controls the conversion and readout processes.
POWER SUPPLY			
AGND	3	Ground	The ground return for the analog supply and signals.
DGND	12	Ground	The ground return for the digital supply and signals.
V <sub>A</sub>	2	Supply Positive analog supply pin. This voltage is also used as the reference voltage. This pin should be connected to a quiet 2.7 V to 5.25 V source and bypassed to GND with $1-\mu$ F and $0.1-\mu$ F monolithic ceramic capacitors located within 1 cm of the power pin.	
V <sub>D</sub>	13	Supply	Positive digital supply pin. This pin should be connected to a 2.7 V to $V_A$ supply, and bypassed to GND with a 0.1- $\mu$ F monolithic ceramic capacitor located within 1 cm of the power pin.

# 6 Specifications

# 6.1 Absolute Maximum Ratings<sup>(1)</sup>

		MIN	MAX	UNIT
VA	Analog supply voltage	-0.3	6.5	V
VD	Digital supply voltage <sup>(2)</sup>	-0.3	V <sub>A</sub> + 0.3	V
	Voltage on any pin to GND	-0.3	V <sub>A</sub> + 0.3	V
	Input current at any pin <sup>(3)</sup>		±10	mA
	Power dissipation $T_A = 25^{\circ}C$		See (4)	
	Package input current <sup>(3)</sup>		±20 mA	mA
	Soldering temperature, 10 seconds		260	°C
	Junction temperature		175	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
 The maximum units is not implied. Exposure to absolute 5.1/2

(2) The maximum voltage is not to exceed 6.5 V

(3) When the input voltage at any pin exceeds the power supplies (that is, V<sub>IN</sub> less than AGND or V<sub>IN</sub> greater than V<sub>A</sub> or V<sub>D</sub>), the current at that pin should be limited to 10 mA. The 20 mA maximum package input current rating limits the number of pins that can safely exceed the power supplies with an input current of 10 mA to two.

(4) The absolute maximum junction temperature (T<sub>J</sub>max) for this device is 175°C. The maximum allowable power dissipation is dictated by T<sub>J</sub>max, the junction-to-ambient thermal resistance (R<sub>0JA</sub>), and the ambient temperature (T<sub>A</sub>), and can be calculated using the formula P<sub>D</sub>MAX = (T<sub>J</sub>max - T<sub>A</sub>)/R<sub>0JA</sub>. The values for maximum power dissipation listed above will be reached only when the ADC128S102QML-SP is operated in a severe fault condition (for example, when input or output pins are driven beyond the power supply voltages, or the power supply polarity is reversed). Obviously, such conditions should always be avoided.

# 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)(2)</sup>	±8000	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) Human body model is 100-pF capacitor discharged through a 1.5-kΩ resistor. Machine model is 220 pF discharged through 0 Ω.

# 6.3 Recommended Operating Conditions

See (1)(2)

	MIN	MAX	UNIT
Operating temperature	-55	125	°C
V <sub>A</sub> supply voltage	2.7	5.25	V
V <sub>D</sub> supply voltage	2.7	V <sub>A</sub>	V
Digital input voltage	0	V <sub>A</sub>	V
Analog input voltage	0	V <sub>A</sub>	V
Clock frequency	0.8	16	MHz

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended Operating Conditions indicate conditions for which the device is functional, but **do not** verify specific performance limits. For specifications and test conditions, see the *Electrical Characteristics*. The specified specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

(2) All voltages are measured with respect to GND = 0 V, unless otherwise specified.

#### ADC128S102QML-SP

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STRUMENTS

EXAS

#### 6.4 Thermal Information

		ACD128S102QML-SP	
	THERMAL METRIC <sup>(1)</sup>	NAC (CFP)	UNIT
		16 PINS	
$R_{\thetaJA}$	Junction-to-ambient thermal resistance	127	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	11.2	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 6.5 Electrical Characteristics: ADC128S102QML-SP Converter

The following specifications apply for AGND = DGND = 0V,  $f_{SCLK}$  = 0.8 MHz to 16 MHz,  $f_{SAMPLE}$  = 50 kSPS to 1 MSPS,  $C_L$  = 50pF, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	SUBGROUP	MIN	TYP <sup>(1)</sup>	MAX	UNIT
STATIO	C CONVERTER CHARACTER	ISTICS					
	Resolution with no missing codes					12	Bits
INL	Integral non-linearity (end	$V_A = V_D = 3 V$	[1, 2, 3]	-1	±0.6	1.1	LSB
	point method)	$V_A = V_D = 5 V$	[1, 2, 3]	-1.25	±0.9	1.4	LSB
		$V_A = V_D = 3 V$	[1, 2, 3]		0.5	0.9	LSB
DNL	Differential non-linearity	$v_A = v_D = 3 v$	[1, 2, 3]	-0.7	-0.3		LSB
DINL	Dinerential non-linearity	$V_A = V_D = 5 V$	[1, 2, 3]		0.9	1.5	LSB
		$v_A = v_D = 5 v$	[1, 2, 3]	-0.9	12 ±0.6 1.1 ±0.9 1.4 0.5 0.9 -0.3	LSB	
v	0	$V_A = V_D = 3 V$	[1, 2, 3]	-2.3	0.8	2.3	LSB
V <sub>OFF</sub>	Offset error	$V_A = V_D = 5 V$	[1, 2, 3]	-2.3	1.1	2.3	LSB
OEM	Offset error match	$V_A = V_D = 3 V$	[1, 2, 3]	-1.5	±0.1	1.5	LSB
	Onset enor match	$V_A = V_D = 5 V$	[1, 2, 3]	-1.5	±0.3	1.5	LSB
FSE	Full scale error	$V_A = V_D = 3 V$	[1, 2, 3]	-2	0.8	2	LSB
01		$V_A = V_D = 5 V$	[1, 2, 3]	-2	0.3	2	LSB
	<b>F</b> ull a sala a man a salah	$V_A = V_D = 3 V$	[1, 2, 3]	-1.5	±0.1	1.5	LSB
FSEIN	Full scale error match	$V_A = V_D = 5 V$	[1, 2, 3]	-1.5	±0.3	1.5	LSB
DYNA	MIC CONVERTER CHARACTE	RISTICS					
FPBW	Full power bandwidth (-3	$V_A = V_D = 3 V$			6.8		MHz
FPDVV	dB)	$V_A = V_D = 5 V$			10		MHz
SINA	Signal-to-noise plus	$V_A = V_D = 3 V,$ f <sub>IN</sub> = 40.2 kHz, -0.02 dBFS	[4, 5, 6]	68	72		dB
D	distortion ratio	$V_A = V_D = 5 V,$ f <sub>IN</sub> = 40.2 kHz, -0.02 dBFS	[4, 5, 6]	68	72		dB
SNR	Signal-to-noise ratio	$V_A = V_D = 3 V$ , $f_{IN} = 40.2 \text{ kHz}$ , -0.02 dBFS	[4, 5, 6]	69	72		dB
SINK	Signal-10-noise ratio	$V_A = V_D = 5 V$ , f <sub>IN</sub> = 40.2 kHz, -0.02 dBFS	[4, 5, 6]	68.5	72		dB
THD	Total harmonic distortion	$V_A = V_D = 3 V,$ $f_{IN} = 40.2 \text{ kHz}, -0.02 \text{ dBFS}$	[4, 5, 6]		-86	-74	dB
עחי		$V_A = V_D = 5 V$ , f <sub>IN</sub> = 40.2 kHz, -0.02 dBFS	[4, 5, 6]		-87	-74	dB
		$V_A = V_D = 3 V,$ $f_{IN} = 40.2 \text{ kHz}, -0.02 \text{ dBFS}$	[4, 5, 6]	75	91		dB
SFUK	Spurious-free dynamic range	$V_A = V_D = 5 V,$ f <sub>IN</sub> = 40.2 kHz, -0.02 dBFS	[4, 5, 6]	75	90		dB

(1) Typical figures are at  $T_J = 25^{\circ}$ C, and represent most likely parametric norms.



#### Electrical Characteristics: ADC128S102QML-SP Converter (continued)

The following specifications apply for AGND = DGND = 0V,  $f_{SCLK} = 0.8$  MHz to 16 MHz,  $f_{SAMPLE} = 50$  kSPS to 1 MSPS,  $C_L = 50$  pF, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	SUBGROUP	MIN	TYP <sup>(1)</sup>	MAX	UNIT
	Effective number of bits	$V_{A} = V_{D} = 3 V,$ $f_{IN} = 40.2 \text{ kHz}$	[4, 5, 6]	11.1	11.6		Bits
		$\label{eq:VA} \begin{array}{l} V_A = V_D = 5 \ V, \\ f_{IN} = 40.2 \ kHz, \ -0.02 \ dBFS \end{array}$	[4, 5, 6]	11.1	11.6		Bits
ISO	Channel-to-channel isolation	$V_A = V_D = 3 V,$ $f_{IN} = 20 \text{ kHz}$			84		dB
00		$V_A = V_D = 5 V,$ $f_{IN} = 20 \text{ kHz}, -0.02 \text{ dBFS}$			85		dB
	Intermodulation distortion,	$V_A = V_D = 3 V,$ $f_a = 19.5 \text{ kHz}, f_b = 20.5 \text{ kHz}$	[4, 5, 6]		-93	-78	dB
IMD	second order terms	$V_A = V_D = 5 V,$ $f_a = 19.5 \text{ kHz}, f_b = 20.5 \text{ kHz}$	[4, 5, 6]		-93	-78	dB
	Intermodulation distortion,	$V_A = V_D = 3 V,$ f <sub>a</sub> = 19.5 kHz, f <sub>b</sub> = 20.5 kHz	[4, 5, 6]		-91	-70	dB
	third order terms	$V_A = V_D = 5 V,$ f <sub>a</sub> = 19.5 kHz, f <sub>b</sub> = 20.5 kHz	[4, 5, 6]		-91	-70	dB
ANALC	OG INPUT CHARACTERISTIC	S				r	
V <sub>IN</sub>	Input range				0 to $V_{A}$		V
I <sub>DCL</sub>	DC leakage current		[1, 2, 3]		±0.01	±1	μA
0	land an a Marca	Track mode, see <sup>(2)</sup>			38		pF
C <sub>INA</sub>	Input capacitance	Hold mode, see <sup>(2)</sup>			4.5		pF
DIGITA	L INPUT CHARACTERISTICS	5	¥			1	
		$V_{A} = V_{D} = 2.7 \text{ V to } 3.6 \text{ V}$	[1, 2, 3]	2.1			V
V <sub>IH</sub>	Input high voltage	$V_{A} = V_{D} = 4.75 \text{ V to } 5.25 \text{ V}$	[1, 2, 3]	2.4			V
V <sub>IL</sub>	Input low voltage	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	[1, 2, 3]			0.8	V
I <sub>IN</sub>	Input current	$V_{IN} = 0 V \text{ or } V_D$	[1, 2, 3]		±1	±1	μA
C <sub>IND</sub>	Digital input capacitance	See <sup>(2)</sup>				3.5	, pF
	L OUTPUT CHARACTERISTI	CS					
V <sub>OH</sub>	Output high voltage	I <sub>SOURCE</sub> = 200 μA, V <sub>A</sub> = V <sub>D</sub> = 2.7 V to 5.25 V	[1, 2, 3]	V <sub>D</sub> -0.5			V
V <sub>OL</sub>	Output low voltage	$I_{SINK} = 200 \ \mu A \text{ to 1 mA},$ $V_A = V_D = 2.7 \ V \text{ to 5.25 V}$	[1, 2, 3]			0.4	V
I <sub>OZH</sub> , I <sub>OZL</sub>	Hi-impedance output leakage current	$V_{A} = V_{D} = 2.7 V \text{ to } 5.25 V$	[1, 2, 3]		±0.01	±1	μA
C <sub>OUT</sub>	Hi-impedance output capacitance	See <sup>(2)</sup>				3.5	pF
	Output coding			Straight	t (Natural)	Binary	
POWE	R SUPPLY CHARACTERISTIC	<b>CS</b> (C <sub>L</sub> = 10 pF)					
V <sub>A</sub> , V <sub>D</sub>	Analog and digital supply	$V_A \ge V_D$	[1, 2, 3]	2.7			V
	voltages		[1, 2, 3]			5.25	V
	Total supply current,	$V_A = V_D = 2.7 V \text{ to } 3.6 V,$ $f_{SAMPLE} = 1 \text{ MSPS}, f_{IN} = 40 \text{ kHz}$	[1, 2, 3]		0.9	1.5	mA
I <sub>A</sub> + I <sub>D</sub>	normal mode ( CS low)	$V_A = V_D = 4.75 V$ to 5.25 V, $f_{SAMPLE} = 1 MSPS$ , $f_{IN} = 40 \text{ kHz}$	[1, 2, 3]		2.2	3.1	mA
A · U	Total supply current,	$\label{eq:VA} \begin{split} V_A = V_D &= 2.7 \ \text{V to } 3.6 \ \text{V}, \\ f_{\text{SCLK}} &= 0 \ \text{kSPS} \end{split}$	[1, 2, 3]		0.11	1	μA
	shutdown mode (CS high)	$V_A = V_D = 4.75 V$ to 5.25 V, $f_{SCLK} = 0 kSPS$	[1, 2, 3]		0.12	1.4	μA

(2) This parameter is specified by design and/or characterization and is not tested in production.

# Electrical Characteristics: ADC128S102QML-SP Converter (continued)

The following specifications apply for AGND = DGND = 0V,  $f_{SCLK} = 0.8$  MHz to 16 MHz,  $f_{SAMPLE} = 50$  kSPS to 1 MSPS,  $C_L = 50$  pF, unless otherwise noted.

	PARAMETER	TEST CON	DITIONS	SUBGROUP	MIN	TYP <sup>(1)</sup>	MAX	UNIT
	Power consumption,	$V_A = V_D = 3 V$ $f_{SAMPLE} = 1 MSPS, f_{IN} =$	$V_A = V_D = 3 V$ $f_{SAMPLE} = 1 MSPS, f_{IN} = 40 \text{ kHz}$			2.7	4.5	mW
Р	normal mode (CS low)	$V_A = V_D = 5 V$ $f_{SAMPLE} = 1 MSPS, f_{IN} =$	[1, 2, 3]		11.0	15.5	mW	
P <sub>C</sub>	Power consumption,	$V_A = V_D = 3 V$ $f_{SCLK} = 0 kSPS$		[1, 2, 3]		0.33	3	μW
	shutdown mode (CS high)	$V_A = V_D = 5 V$ $f_{SCLK} = 0 kSPS$	[1, 2, 3]		0.6	7	μW	
AC EL	ECTRICAL CHARACTERISTI	CS						
f <sub>SCLK</sub> MIN	Minimum clock frequency	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	V	[9, 10, 11]	0.8			MHz
f <sub>SCLK</sub>	Maximum clock frequency	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	V	[9, 10, 11]			16	MHz
4	Sample rate continuous		1	[9, 10, 11]	50			kSPS
f <sub>S</sub>	mode	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	[9, 10, 11]			1	MSPS	
t <sub>CONVE</sub> RT	Conversion (hold) time	$V_A = V_D = 2.7 V$ to 5.25 V	V	[9, 10, 11]			13	SCLK cycles
DC	SCLK duty cycle	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25$	MIN			40%		
DC	SOLK duly cycle	V	MAX			60%		
t <sub>ACQ</sub>	Acquisition (track) time	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	V	[9, 10, 11]			3	SCLK cycles
	Throughput time	Acquisition time + convert $V_A = V_D = 2.7 V$ to 5.25 V		[9, 10, 11]			16	SCLK cycles
t <sub>AD</sub>	Aperture delay	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	V			4		ns

# 6.6 Electrical Characteristics: Radiation

The following specifications apply for V<sub>A</sub> = V<sub>D</sub> = 2.7 V to 5.25 V, AGND = DGND = 0 V,  $f_{SCLK}$  = 0.8 MHz to 16 MHz,  $f_{SAMPLE}$  = 50 kSPS to 1 MSPS, and C<sub>L</sub> = 50 pF.<sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	SUBGROUP	MIN TYP	MAX	UNIT
I <sub>A</sub> + I <sub>D</sub>	Total supply current shutdown mode	$V_A = V_D = 2.7 V$ to 3.6 V, $f_{SCLK} = 0 kSPS$	[1]		30	μA
	(CS high)	$V_A = V_D = 4.75 V$ to 5.25 V, $f_{SCLK} = 0 kSPS$	[1]		100	μA
I <sub>OZH</sub> , I <sub>OZL</sub>	Hi-impedance output leakage current	$V_{A} = V_{D} = 2.7 \text{ V to } 5.25 \text{ V}$	[1]		±10	μA

(1) Pre and post irradiation limits are identical to those listed in the *DC Parameters* and *AC and Timing Characteristics*, except as listed in *Electrical Characteristics: Radiation.* When performing post irradiation electrical measurements for any RHA level, T<sub>A</sub> = 25°C.



# 6.7 Electrical Characteristics: Burn in Delta Parameters - T<sub>A</sub> at 25°C

The following specifications apply for V<sub>A</sub> = V<sub>D</sub> = 2.7 V to 5.25 V, AGND = DGND = 0 V,  $f_{SCLK}$  = 0.8 MHz to 16 MHz,  $f_{SAMPLE}$  = 50 kSPS to 1 MSPS, and C<sub>L</sub> = 50 pF.<sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
INL	Integral populized rity	$V_A = V_D = 3 V$	-0.5	0.106	0.5	LSB
	Integral non-linearity	$V_A = V_D = 5 V$	-0.35	0.016	0.35	LSB
IN ID	Intermodulation distortion,	$V_A = V_D = 3 V$	-14	1.35	14	dB
IMD	second order terms	$V_A = V_D = 5 V$	-17	1.67	17	dB
IMD	Intermodulation distortion, third	$V_A = V_D = 3 V$	-10	0.47	10	dB
	order terms	$V_A = V_D = 5 V$	-10	0.9	10	dB

(1) This is worse case drift, Deltas are performed at room temperature post operational life. All other parameters, no deltas are required.

## 6.8 Timing Requirements

The following specifications apply for  $V_A = V_D = 2.7$  V to 5.25 V, AGND = DGND = 0 V,  $f_{SCLK} = 0.8$  MHz to 16 MHz,  $f_{SAMPLE} = 0.8$  MHz to 16 MHz 50 kSPS to 1 MSPS, and  $C_L = 50 \text{ pF}$ .

			SUBGROUP	MIN	NOM <sup>(1)</sup>	MAX	UNIT
t <sub>CSH</sub>	CS hold time after SCLK rising edge	See <sup>(2)</sup>	[9, 10, 11]	10	0		ns
t <sub>CSS</sub>	CS setup time prior to SCLK rising edge	See <sup>(2)</sup>	[9, 10, 11]	10	4.5		ns
t <sub>EN</sub>	CS falling edge to DOUT enable	d	[9, 10, 11]		5	30	ns
t <sub>DACC</sub>	DOUT access time after SCLK f	alling edge	[9, 10, 11]		17	27	ns
t <sub>DHLD</sub>	DOUT hold time after SCLK falli	ng edge	[9, 10, 11]	7			ns
t <sub>DS</sub>	DIN setup time prior to SCLK ris	ing edge	[9, 10, 11]	10			ns
t <sub>DH</sub>	DIN hold time after SCLK rising	edge	[9, 10, 11]	10			ns
t <sub>CH</sub>	SCLK high time				0.4 × t <sub>SCLK</sub>		ns
t <sub>CL</sub>	SCLK low time			0.4 × t <sub>SCLK</sub>			ns
+	CS rising edge to DOUT high-	DOUT falling	[9, 10, 11]		2.4	20	ns
t <sub>DIS</sub>	impedance	DOUT rising	[9, 10, 11]		0.9	20	ns

Typical figures are at T<sub>J</sub> = 25°C, and represent most likely parametric norms.
 Clock may be in any state (high or low) when CS goes high. Setup and hold time restrictions apply only to CS going low.

#### Table 1. Quality Conformance Inspection<sup>(1)</sup>

SUBGROUP	DESCRIPTION	TEMP (°C)		
1	Static tests at	25		
2	Static tests at	125		
3	Static tests at	-55		
4	Dynamic tests at	25		
5	Dynamic tests at	125		
6	Dynamic tests at	-55		
7	Functional tests at	25		
8A	Functional tests at	125		
8B	Functional tests at	-55		
9	Switching tests at	25		
10	Switching tests at	125		
11	Switching tests at	-55		
12	Setting time at	25		
13	Setting time at	125		
14	Setting time at	-55		

(1) MIL-STD-883, Method 5005 - Group A

Power Down Power Up Power Up Hold Track Hold Track CS 15 9 10 12 13 14 16 2 5 8 6 SCLK Control register N + 1 Control register N XXXXXXXXXX ADD1 ADD0 ADD2 ADD1 ADD DIN ADD2 XXXXXXX Data N – 1 Data N DB9 DOUT . DB11 DB10 DB6 DB3 DB1 DB0 DB1 DB10 DB9 FOUR ZEROS DB8 DB7 DB5 DB4 DB2 FOUR ZEROS

Figure 1. ADC128S102 Operational Timing Diagram



Figure 2. ADC128S102 Serial Timing Diagram



Figure 3. SCLK and CS Timing Parameters



### 6.9 Typical Characteristics

 $T_{\text{A}}$  = 25°C,  $f_{\text{SAMPLE}}$  = 1 MSPS,  $f_{\text{SCLK}}$  = 16 MHz,  $f_{\text{IN}}$  = 40.2 kHz unless otherwise stated.



# **Typical Characteristics (continued)**

 $T_A = 25^{\circ}C$ ,  $f_{SAMPLE} = 1$  MSPS,  $f_{SCLK} = 16$  MHz,  $f_{IN} = 40.2$  kHz unless otherwise stated.





#### **Typical Characteristics (continued)**



 $T_A = 25^{\circ}C$ ,  $f_{SAMPLE} = 1$  MSPS,  $f_{SCLK} = 16$  MHz,  $f_{IN} = 40.2$  kHz unless otherwise stated.

# **Typical Characteristics (continued)**

 $T_A = 25^{\circ}C$ ,  $f_{SAMPLE} = 1$  MSPS,  $f_{SCLK} = 16$  MHz,  $f_{IN} = 40.2$  kHz unless otherwise stated.





#### ADC128S102QML-SP SNAS411P – AUGUST 2008– REVISED APRIL 2017

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### **Typical Characteristics (continued)**



ADC128S102QML-SP SNAS411P – AUGUST 2008 – REVISED APRIL 2017



### 7 Detailed Description

#### 7.1 Overview

The ADC128S102 is a successive-approximation analog-to-digital converter designed around a charge redistribution digital-to-analog converter.

#### 7.2 Functional Block Diagram



#### 7.3 Feature Description

#### 7.3.1 ADC128S102 Transfer Function

The output format of the ADC128S102 is straight binary. Code transitions occur midway between successive integer LSB values. The LSB width for the ADC128S102 is  $V_A$  / 4096. The ideal transfer characteristic is shown in Figure 34. The transition from an output code of 0000 0000 0000 to a code of 0000 0000 0001 is at 1/2 LSB, or a voltage of  $V_A$  / 8192. Other code transitions occur at steps of one LSB.



#### **Feature Description (continued)**



Figure 34. Ideal Transfer Characteristic

#### 7.3.2 Analog Inputs

An equivalent circuit for one of the input channels of the ADC128S102 is shown in Figure 35. Diodes D1 and D2 provide ESD protection for the analog inputs. The operating range for the analog inputs is 0 V to  $V_A$ . Going beyond this range will cause the ESD diodes to conduct and result in erratic operation.

The capacitor C1 in Figure 35 has a typical value of 3 pF and is mainly the package pin capacitance. Resistor R1 is the ON-resistance of the multiplexer and track or hold switch and is typically 500  $\Omega$ . Capacitor C2 is the ADC128S102 sampling capacitor, and is typically 30 pF. The ADC128S102 will deliver best performance when driven by a low-impedance source (less than 100  $\Omega$ ). This is especially important when using the ADC128S102 to sample dynamic signals. Also important when sampling dynamic signals is a band-pass or low-pass filter which reduces harmonics and noise in the input. These filters are often referred to as anti-aliasing filters.



Figure 35. Equivalent Input Circuit

#### 7.3.3 Digital Inputs and Outputs

The digital inputs of the ADC128S102 (SCLK,  $\overline{CS}$ , and DIN) have an operating range of 0 V to V<sub>A</sub>. The inputs are not prone to latch-up and may be asserted before the digital supply (V<sub>D</sub>) without any risk. The digital output (DOUT) operating range is controlled by V<sub>D</sub>. The output high voltage is V<sub>D</sub> – 0.5 V (minimum) while the output low voltage is 0.4 V (maximum).

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#### **Feature Description (continued)**

#### 7.3.4 Radiation Environments

Careful consideration should be given to environmental conditions when using a product in a radiation environment.

#### 7.3.4.1 Total lonizing Dose

Radiation hardness assured (RHA) products are those part numbers with a total ionizing dose (TID) level listed in the *Device Information* table in the *Description* section. Testing and qualification of these products is done on a wafer level according to *MIL-STD-883G*, *Test Method 1019.7*. Testing is done according to Condition A and the Extended room temperature anneal test described in section 3.11 for application environment dose rates less than 0.027 rad(Si)/s. Wafer level TID data is available with lot shipments.

#### 7.3.4.2 Single Event Latch-Up and Functional Interrupt

One-time single event latch-up (SEL) and single event functional interrupt (SEFI) testing was preformed according to EIA/JEDEC Standard, EIA/JEDEC57. The linear energy transfer threshold (LETth) shown in *Features* is the maximum LET tested. A test report is available upon request.

#### 7.3.4.3 Single Event Upset

A report on single event upset (SEU) is available upon request.

#### 7.4 Device Functional Modes

#### 7.4.1 ADC128S102 Operation

Simplified schematics of the ADC128S102 in both track and hold operation are shown in Figure 36 and Figure 37 respectively. In Figure 36, the ADC128S102 is in track mode: switch SW1 connects the sampling capacitor to one of eight analog input channels through the multiplexer, and SW2 balances the comparator inputs. The ADC128S102 is in this state for the first three SCLK cycles after CS is brought low.

Figure 37 shows the ADC128S102 in hold mode: switch SW1 connects the sampling capacitor to ground, maintaining the sampled voltage, and switch SW2 unbalances the comparator. The control logic then instructs the charge-redistribution DAC to add or subtract fixed amounts of charge to or from the sampling capacitor until the comparator is balanced. When the comparator is balanced, the digital word supplied to the DAC is the digital representation of the analog input voltage. The ADC128S102 is in this state for the last thirteen SCLK cycles after  $\overline{CS}$  is brought low.



Figure 36. ADC128S102 in Track Mode



#### **Device Functional Modes (continued)**



Figure 37. ADC128S102 in Hold Mode

#### 7.5 Programming

#### 7.5.1 Serial Interface

An operational timing diagram and a serial interface timing diagram for the ADC128S102 are shown in Figure 1 to Figure 3. CS, chip select, initiates conversions and frames the serial data transfers. SCLK (serial clock) controls both the conversion process and the timing of serial data. DOUT is the serial data output pin, where a conversion result is sent as a serial data stream, MSB first. Data to be written to the ADC128S102's Control Register is placed on DIN, the serial data input pin. New data is written to DIN with each conversion.

A serial frame is initiated on the falling edge of  $\overline{CS}$  and ends on the rising edge of  $\overline{CS}$ . Each frame must contain an integer multiple of 16 rising SCLK edges. The ADC's DOUT pin is in a high impedance state when  $\overline{CS}$  is high and is active when  $\overline{CS}$  is low. Note that  $\overline{CS}$  is asynchronous. Thus,  $\overline{CS}$  acts as an output enable. Similarly, SCLK is internally gated off when  $\overline{CS}$  is brought high.

During the first 3 cycles of SCLK, the ADC is in the track mode, acquiring the input voltage. For the next 13 SCLK cycles the conversion is accomplished and the data is clocked out. SCLK falling edges 1 through 4 clock out leading zeros while falling edges 5 through 16 clock out the conversion result, MSB first. If there is more than one conversion in a frame (continuous conversion mode), the ADC will re-enter the track mode on the falling edge of SCLK after the N\*16th rising edge of SCLK and re-enter the hold/convert mode on the N×16+4th falling edge of SCLK. "N" is an integer value.

The ADC128S102 enters track mode under three different conditions. In Figure 1,  $\overline{CS}$  goes low with SCLK high and the ADC enters track mode on the first falling edge of SCLK. In the second condition,  $\overline{CS}$  goes low with SCLK low. Under this condition, the ADC automatically enters track mode and the falling edge of  $\overline{CS}$  is seen as the first falling edge of SCLK. In the third condition,  $\overline{CS}$  and SCLK go low simultaneously and the ADC enters track mode. While there is no timing restriction with respect to the falling edges of  $\overline{CS}$  and SCLK, see Figure 3 for setup and hold time requirements for the falling edge of  $\overline{CS}$  with respect to the rising edge of SCLK.

During each conversion, data is clocked into a control register through the DIN pin on the first 8 rising edges of SCLK after the fall of CS. The control register is loaded with data indicating the input channel to be converted on the subsequent conversion (see Table 2, Table 3, and Table 4).

Although the ADC128S102 is able to acquire the input signal to full resolution in the first conversion immediately following power-up, the first conversion result after power-up will be that of a randomly selected channel. Therefore, the user needs to incorporate a dummy conversion to set the required channel that will be used on the subsequent conversion.

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# **Programming (continued)**

#### Table 2. Control Register Bits

BIT 7 (MSB)	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0
DONTC	DONTC	ADD2	ADD1	ADD0	DONTC	DONTC	DONTC

#### Table 3. Control Register Bit Descriptions

BIT	SYMBOL	DESCRIPTION
7, 6, 2, 1, 0	DONTC	Don't care. The values of these bits do not affect the device.
5	ADD2	These three bits determine which input channel will be sampled and converted at the next conversion cycle.
4	ADD1	The mapping between codes and channels is shown in Table 4.
3	ADD0	

#### **Table 4. Input Channel Selection**

ADD2	ADD1	ADD0	INPUT CHANNEL
0	0	0	IN0
0	0	1	IN1
0	1	0	IN2
0	1	1	IN3
1	0	0	IN4
1	0	1	IN5
1	1	0	IN6
1	1	1	IN7



## 8 Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 8.1 Application Information

The ADC128S102 device is a low-power, eight-channel 12-bit ADC with ensured performance specifications from 50 kSPS to 1 MSPS. It is appropriate to utilize the ADC128S102 at sample rates below 50 kSPS by powering the device down (de-asserting CSB) in between conversions. The Electrical Characteristics information highlights the clock frequency where the ADC's performance is ensured. There is no limitation on periods of time for shutdown between conversions.

#### 8.2 Typical Application

A typical application is shown in Figure 38. The split analog and digital supply pins are both powered in this example by the Texas Instruments LP2950-N low-dropout voltage regulator. The analog supply is bypassed with a capacitor network located close to the ADC128S102. The digital supply is separated from the analog supply by an isolation resistor and bypassed with additional capacitors. The ADC128S102 uses the analog supply ( $V_A$ ) as its reference voltage, so it is very important that  $V_A$  be kept as clean as possible. Due to the low power requirements of the ADC128S102, it is also possible to use a precision reference as a power supply.





#### 8.2.1 Design Requirements

A positive supply only data acquisition system capable of digitizing up to eight single-ended input signals ranging from 0 to 5 V with BW = 10 kHz and a throughput up to 500 kSPS. The ADC128S102 has to interface to an MCU whose supply is set at 5 V. If it is necessary to interface with an MCU that operates at 3.3 V or lower, VA and VD will need to be separated and care must be taken to ensure that VA is powered before VD.



## **Typical Application (continued)**

#### 8.2.2 Detailed Design Procedure

The signal range requirement forces the design to use 5-V analog supply at VA, analog supply. This follows from the fact that VA is also a reference potential for the ADC. If the requirement of interfacing to the MCU changes to 3.3-V, it will be necessary to change the VD supply voltage to 3.3 V. The maximum sampling rate of the ADC128S102 when all channels (eight) are enabled is,  $Fs = F_{SCLK} / (16 \times 8)$ .

Note that faster sampling rates can be achieved when fewer channels are sampled. Single channel can be sampled at the maximum rate of Fs (single) =  $F_{SCLK}$  / 16.

The VA and VD pins are separated by a  $51-\Omega$  resistor in order to minimize digital noise from corrupting the analog reference input. If additional filtering is required, the resistor can be replaced by a ferrite bead, thus achieving a 2nd-order filter response. Further noise consideration could be given to the SPI interface, especially when the master MCU is capable of producing fast rising edges on the digital bus signals. Inserting small resistances in the digital signal path may help in reducing the ground bounce, and thus improve the overall noise performance of the system. Care should be taken when the signal source is capable of producing voltages beyond VA. In such instances, the internal ESD diodes may start conducting. The ESD diodes are not intended as input signal clamps. To provide the desired clamping action use Schottky diodes.

#### 8.2.3 Application Curve



Figure 39. ENOB vs Temperature



## 9 Power Supply Recommendations

There are three major power supply concerns with this product: power supply sequencing, power management, and the effect of digital supply noise on the analog supply.

#### 9.1 Power Supply Sequence

The ADC128S102 is a dual-supply device. The two supply pins share ESD resources, so care must be exercised to ensure that the power is applied in the correct sequence. To avoid turning on the ESD diodes, the digital supply ( $V_D$ ) cannot exceed the analog supply ( $V_A$ ) by more than 300 mV, during a conversion cycle. Therefore,  $V_A$  must ramp up before or concurrently with  $V_D$ .

#### 9.2 Power Management

The ADC128S102 is fully powered-up whenever  $\overline{CS}$  is low and fully powered-down whenever  $\overline{CS}$  is high, with one exception. If operating in continuous conversion mode, the ADC128S102 automatically enters power-down mode between SCLK's 16th falling edge of a conversion and SCLK's 1st falling edge of the subsequent conversion (see Figure 1).

In continuous conversion mode, the ADC128S102 can perform multiple conversions back to back. Each conversion requires 16 SCLK cycles and the ADC128S102 will perform conversions continuously as long as  $\overline{CS}$  is held low. Continuous mode offers maximum throughput.

In burst mode, the user may trade off throughput for power consumption by performing fewer conversions per unit time. This means spending more time in power-down mode and less time in normal mode. By utilizing this technique, the user can achieve very low sample rates while still utilizing an SCLK frequency within the electrical specifications. The Power Consumption versus SCLK curve in the *Typical Characteristics* shows the typical power consumption of the ADC128S102. To calculate the power consumption ( $P_c$ ), simply multiply the fraction of time spent in the normal mode ( $t_N$ ) by the normal mode power consumption ( $P_N$ ), and add the fraction of time spent in shutdown mode ( $t_S$ ) multiplied by the shutdown mode power consumption ( $P_S$ ) as shown in Equation 1.

$$\mathbf{P}_{\mathbf{C}} = \frac{\mathbf{t}_{\mathbf{N}}}{\mathbf{t}_{\mathbf{N}} + \mathbf{t}_{\mathbf{S}}} \times \mathbf{P}_{\mathbf{N}} + \frac{\mathbf{t}_{\mathbf{S}}}{\mathbf{t}_{\mathbf{N}} + \mathbf{t}_{\mathbf{S}}} \times \mathbf{P}_{\mathbf{S}}$$

(1)

#### 9.3 **Power Supply Noise Considerations**

The charging of any output load capacitance requires current from the digital supply,  $V_D$ . The current pulses required from the supply to charge the output capacitance will cause voltage variations on the digital supply. If these variations are large enough, they could degrade SNR and SINAD performance of the ADC. Furthermore, if the analog and digital supplies are tied directly together, the noise on the digital supply will be coupled directly into the analog supply, causing greater performance degradation than would noise on the digital supply alone. Similarly, discharging the output capacitance when the digital output goes from a logic high to a logic low will dump current into the die substrate, which is resistive. Load discharge currents will cause "ground bounce" noise in the substrate that will degrade noise performance if that current is large enough. The larger the output capacitance, the more current flows through the die substrate and the greater the noise coupled into the analog channel.

The first solution to keeping digital noise out of the analog supply is to decouple the analog and digital supplies from each other or use separate supplies for them. To keep noise out of the digital supply, keep the output load capacitance as small as practical. If the load capacitance is greater than 50 pF, use a 100- $\Omega$  series resistor at the ADC output, located as close to the ADC output pin as practical. This will limit the charge and discharge current of the output capacitance and improve noise performance. Because the series resistor and the load capacitance form a low frequency pole, verify signal integrity once the series resistor has been added.

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## 10 Layout

#### 10.1 Layout Guidelines

Capacitive coupling between the noisy digital circuitry and the sensitive analog circuitry can lead to poor performance. The solution is to keep the analog circuitry separated from the digital circuitry and the clock line as short as possible.

Digital circuits create substantial supply and ground current transients. The logic noise generated could have significant impact upon system noise performance. To avoid performance degradation of the ADC128S102 due to supply noise, do not use the same supply for the ADC128S102 that is used for digital logic.

Generally, analog and digital lines should cross each other at 90° to avoid crosstalk. However, to maximize accuracy in high resolution systems, avoid crossing analog and digital lines altogether. It is important to keep clock lines as short as possible and isolated from ALL other lines, including other digital lines. In addition, the clock line should also be treated as a transmission line and be properly terminated.

The analog input should be isolated from noisy signal traces to avoid coupling of spurious signals into the input. Any external component (for example, a filter capacitor) connected between the converter's input pins and ground or to the reference input pin and ground should be connected to a very clean point in the ground plane.

We recommend the use of a single, uniform ground plane and the use of split power planes. The power planes should be located within the same board layer. All analog circuitry (input amplifiers, filters, reference components, and so forth) should be placed over the analog power plane. All digital circuitry and I/O lines should be placed over the digital power plane. Furthermore, all components in the reference circuitry and the input signal chain that are connected to ground should be connected together with short traces and enter the analog ground plane at a single, quiet point.



# 10.2 Layout Example





# 11 Device and Documentation Support

### 11.1 Device Support

#### 11.1.1 Development Support

For related documentation, see the following:

- 5962R07727
- Radiation Report
- MIL-STD-883G, Test Method 1019.7

#### 11.1.2 Device Nomenclature

#### 11.1.2.1 Specification Definitions

- **ACQUISITION TIME** is the time required for the ADC to acquire the input voltage. During this time, the hold capacitor is charged by the input voltage.
- **APERTURE DELAY** is the time between the fourth falling edge of SCLK and the time when the input signal is internally acquired or held for conversion.
- **CHANNEL-TO-CHANNEL ISOLATION** is resistance to coupling of energy from one channel into another channel.
- **CONVERSION TIME** is the time required, after the input voltage is acquired, for the ADC to convert the input voltage to a digital word.
- **CROSSTALK** is the coupling of energy from one channel into another channel. This is similar to Channel-to-Channel Isolation, except for the sign of the data.
- **DIFFERENTIAL NON-LINEARITY (DNL)** is the measure of the maximum deviation from the ideal step size of 1 LSB.
- **DUTY CYCLE** is the ratio of the time that a repetitive digital waveform is high to the total time of one period. The specification here refers to the SCLK.
- **EFFECTIVE NUMBER OF BITS (ENOB, or EFFECTIVE BITS)** is another method of specifying Signal-to-Noise and Distortion or SINAD. ENOB is defined as (SINAD 1.76) / 6.02 and says that the converter is equivalent to a perfect ADC of this (ENOB) number of bits.
- **FULL POWER BANDWIDTH** is a measure of the frequency at which the reconstructed output fundamental drops 3 dB below its low frequency value for a full scale input.
- GAIN ERROR is the deviation of the last code transition (111...110) to (111...111) from the ideal (V<sub>REF</sub> 1.5 LSB), after adjusting for offset error.
- **INTEGRAL NON-LINEARITY (INL)** is a measure of the deviation of each individual code from a line drawn from negative full scale (½ LSB below the first code transition) through positive full scale (½ LSB above the last code transition). The deviation of any given code from this straight line is measured from the center of that code value.
- **INTERMODULATION DISTORTION (IMD)** is the creation of additional spectral components as a result of two sinusoidal frequencies being applied to an individual ADC input at the same time. It is defined as the ratio of the power in either the second or the third order intermodulation products to the sum of the power in both of the original frequencies. Second order products are  $f_a \pm f_b$ , where  $f_a$  and  $f_b$  are the two sine wave input frequencies. Third order products are  $(2f_a \pm f_b)$  and  $(f_a \pm 2f_b)$ . IMD is usually expressed in dB.
- **MISSING CODES** are those output codes that will never appear at the ADC outputs. The ADC128S102 is verified not to have any missing codes.
- **OFFSET ERROR** is the deviation of the first code transition (000...000) to (000...001) from the ideal (that is, GND + 0.5 LSB).
- SIGNAL TO NOISE RATIO (SNR) is the ratio, expressed in dB, of the rms value of the input signal to the rms value of the sum of all other spectral components below one-half the sampling frequency, not

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#### **Device Support (continued)**

including harmonics or d.c.

- SIGNAL TO NOISE PLUS DISTORTION (S/N+D or SINAD) Is the ratio, expressed in dB, of the rms value of the input signal to the rms value of all of the other spectral components below half the clock frequency, including harmonics but excluding d.c.
- **SPURIOUS FREE DYNAMIC RANGE (SFDR)** is the difference, expressed in dB, between the desired signal amplitude to the amplitude of the peak spurious spectral component, where a spurious spectral component is any signal present in the output spectrum that is not present at the input and may or may not be a harmonic.
- **THROUGHPUT TIME** is the minimum time required between the start of two successive conversions. It is the acquisition time plus the conversion time.
- **TOTAL HARMONIC DISTORTION (THD)** is the ratio, expressed in dBc, of the rms total of the first five harmonic components at the output to the rms level of the input signal frequency as seen at the output. THD is calculated as:

THD = 20 · log<sub>10</sub> 
$$\sqrt{\frac{A_{f2}^2 + \dots + A_{f10}^2}{A_{f1}^2}}$$

where

- A<sub>f1</sub> is the RMS power of the input frequency at the output
- A<sub>f2</sub> through A<sub>f10</sub> are the RMS power in the first 9 harmonic frequencies

(2)

## **11.2** Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

# **11.3 Community Resources**

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration

among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

# 11.4 Trademarks

MICROWIRE, E2E are trademarks of Texas Instruments. SPI, QSPI are trademarks of Motorola, Inc.. All other trademarks are the property of their respective owners.

#### **11.5 Electrostatic Discharge Caution**



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

# 11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.



## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

#### 12.1 Engineering Samples

Engineering samples are available for order and are identified by the "MPR" in the orderable device name (see Packaging Information in the Addendum). Engineering (MPR) samples meet the performance specifications of the datasheet at room temperature only and have not received the full space production flow or testing. Engineering samples may be QCI rejects that failed tests that would not impact the performance at room temperature, such as radiation or reliability testing.



# **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962R0722701V9A	ACTIVE	DIESALE	Y	0	20	RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125		Samples
5962R0722701VFA	ACTIVE	CFP	NAD	16	19	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	ADC128S102 WRQMLV Q 5962R07227 01VFA ACO 01VFA >T	Samples
5962R0722701VZA	ACTIVE	CFP	NAC	16	42	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	ADC128S102 WGRQMLV Q 5962R07227 01VZA ACO 01VZA >T	Samples
ADC128S102 MDR	ACTIVE	DIESALE	Y	0	20	RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125		Samples
ADC128S102WGMPR	ACTIVE	CFP	NAC	16	42	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	25 to 25	ADC128S102 WGMPR ES ACO WGMPR ES >T	Samples
ADC128S102WGRQV	ACTIVE	CFP	NAC	16	42	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	ADC128S102 WGRQMLV Q 5962R07227 01VZA ACO 01VZA >T	Samples
ADC128S102WRQV	ACTIVE	CFP	NAD	16	19	Non-RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	ADC128S102 WRQMLV Q 5962R07227 01VFA ACO 01VFA >T	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs. LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect. NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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5-Jan-2022

# TUBE



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
5962R0722701VFA	NAD	CFP	16	19	502	23	9398	9.78
ADC128S102WRQV	NAD	CFP	16	19	502	23	9398	9.78

# PACKAGE MATERIALS INFORMATION

5-Jan-2022

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**INSTRUMENTS** 

#### TRAY



Chamfer on Tray corner indicates Pin 1 orientation of packed units.

Device	Package Name	Package Type	Pins	SPQ	Unit array matrix	Max temperature (°C)	L (mm)	W (mm)	K0 (µm)	P1 (mm)	CL (mm)	CW (mm)
5962R0722701VZA	NAC	CFP	16	42	7 X 6	NA	101.6	101.6	8001	2.84	15.24	15.24
ADC128S102WGMPR	NAC	CFP	16	42	7 X 6	NA	101.6	101.6	8001	2.84	15.24	15.24
ADC128S102WGRQV	NAC	CFP	16	42	7 X 6	NA	101.6	101.6	8001	2.84	15.24	15.24

\*All dimensions are nominal

# **NAC0016A**



# **PACKAGE OUTLINE**

# CFP - 2.33mm max height

CERAMIC FLATPACK



NOTES:

- Controlling dimension is Inch. Values in [] are milimeters. Dimensions in () for reference only.
   For solder thickness and composition, see the "Lead Finish Composition/Thickness" link in the packaging section of the
- Texas Instruments website 3. Lead 1 identification shall be:
- a) A notch or other mark within this area
- b) A tab on lead 1, either side
- 4. No JEDEC registration as of December 2021



# NAC0016A

# **EXAMPLE BOARD LAYOUT**

# CFP - 2.33mm max height

CERAMIC FLATPACK





	REVISIONS									
REV	DESCRIPTION	E.C.N.	DATE	BY/APP'D						
Α	RELEASE TO DOCUMENT CONTROL	2197879	12/30/2021	TINA TRAN / ANIS FAUZI						
В	NO CHANGE TO DRAWING; REVISION FOR YODA RELEASE;	2198832	02/15/2022	K. SINCERBOX						
С	.387±.003 WAS .39000±.00012;	2200917	08/08/2022	D. CHIN / K. SINCERBOX						

SCALE	size A	4215108	REV C	PAGE 4 of 4
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